

## R-C Thermal Model Parameters

### DESCRIPTION

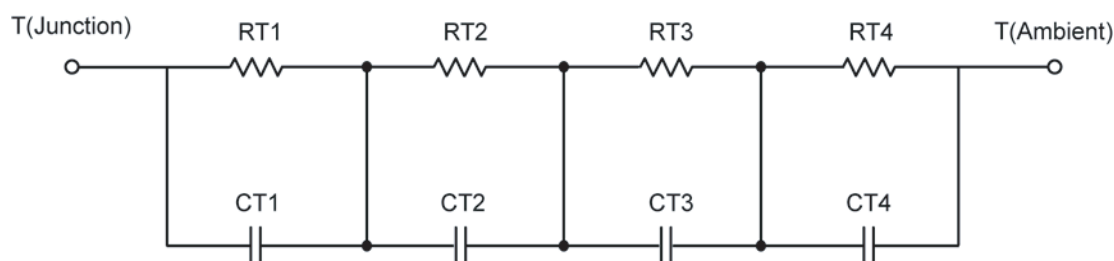
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

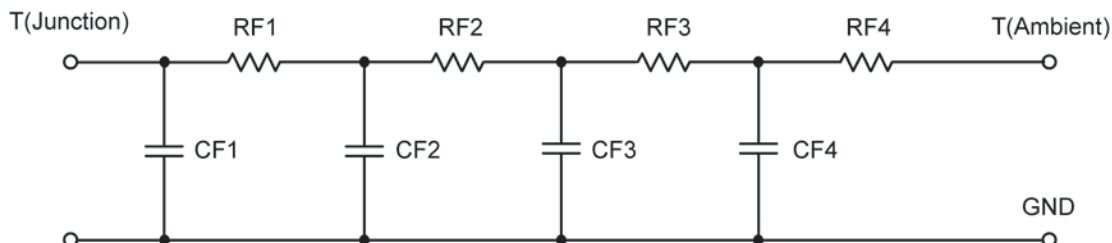
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	20.7160	N/A	17.1389
RT2	5.5506	N/A	3.9724
RT3	27.9011	N/A	9.8622
RT4	55.6595	N/A	8.8776
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	11.7362 m	N/A	2.4908 m
CT2	1.5339 m	N/A	285.8137 u
CT3	60.6292 m	N/A	15.2904 m
CT4	1.3777	N/A	93.4063 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	8.0294	N/A	4.5113
RF2	27.9960	N/A	24.0737
RF3	22.8634	N/A	10.5751
RF4	51.2115	N/A	1.2756
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	1.5740 m	N/A	207.0248 u
CF2	9.0222 m	N/A	1.8986 m
CF3	81.6519 m	N/A	41.4354 m
CF4	1.4719	N/A	10.4137

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

